

H11AA814 Series, H11A617 Series, H11A817 Series 4-Pin Phototransistor Optocouplers

Features

- AC input response (H11AA814 only)
- Compatible to Pb-free IR reflow soldering
- Compact 4-pin dual in-line package
- Current transfer ratio in selected groups: H11AA814: 20-300% H11A817: 50-600%
 H11AA814A: 50-150% H11A817A: 80-160%
 H11A617A: 40%-80% H11A817B: 130-260%
 H11A617B: 63%-125% H11A817C: 200-400%
 H11A617C: 100%-200% H11A817D: 300-600%
 H11A617D: 160%-320%
- C-UL, UL and VDE approved
- High input-output isolation voltage of 5000Vrms
- Minimum BV_{CEO} of 70V guaranteed

Applications

- H11AA814 Series
- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

H11A617 and H11A817 Series

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

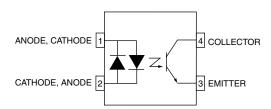
Description

The H11AA814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a silicon phototransistor output in a 4-pin dual in-line package. The H11A617/817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

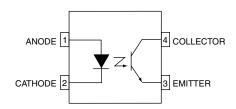
Package

Schematics

H11AA814



H11A617 & H11A817



July 2006

Symbol	Parameter	Device*	Value	Units
TOTAL DE	VICE			
T _{STG}	Storage Temperature	emperature All		°C
T _{OPR}	Operating Temperature	All	-55 to +100	°C
T _{SOL}	Lead Solder Temperature	All	260 for 10 sec	°C
PD	Total Device Power Dissipation (-55°C to 50°C)	All	200	mW
EMITTER				
١ _F	Continuous Forward Current	814 Series 617, 817 Series	±50 50	mA
V _R	Reverse Voltage	617 Series 817 Series	6 6	V
P _D	LED Power Dissipation (25°C ambient) No derating up to 100°C	All	70	mW
DETECTO	Ŕ			
V _{CEO}	Collector-Emitter Voltage	All	70	V
V_{ECO}	Emitter-Collector Voltage	814, 817 Series 617 Series	6 7	V
۱ _C	Continuous Collector Current	All	50	mA
PD	Detector Power Dissipation (25°C ambient)	All	150	mW
Derate	Derate above 90°C		2.9	mW/°C

Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified.)

Electrical Characteristics (T_A = 25°C Unless otherwise specified.) **Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit	
EMITTER								
V _F Input Forward Voltage	Input Forward Voltage	I _F = 60mA	617 Series		1.2 1 1.2 1 .001 1 100 1	1.65	V	
		I _F = 20mA	817 Series		1.2	1.5		
		$I_F = \pm 20 \text{mA}$	814 Series		1.2	1.5		
I _R Reverse Leakage	V _R = 6.0V	617 Series		.001	10	μA		
	Current	V _R = 5.0V	817 Series	1				
DETECTO	R							
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm F} = 0$	ALL	70	100		V	
BV _{ECO}	Emitter-Collector	I _E = 10 μA, I _F = 0	814, 817 Series	6	10		V	
	Breakdown Voltage	Breakdown Voltage	Breakdown Voltage	617 Series	7	10		
I _{CEO} Collector-Emitter Dark Current		V _{CE} = 10V, I _F = 0	H11AA814/A, 817 Series, H11A617C/D		1	100	nA	
			H11A617A/B	1		50		

*Typical values at $T_A=25^{\circ}C$

Symbol	DC Characteristic	Test Conditions	Device	Min	Тур*	Max	Unit
CTR	Current Transfer	$I_{F} = \pm 1 \text{mA}, V_{CE} = 5V^{(1)}$	H11AA814	20		300	%
	Ratio	$I_{F} = \pm 1 \text{mA}, V_{CE} = 5V^{(1)}$	H11AA814A	50		150	%
		$(I_F = 10 \text{mA}, V_{CE} = 5 \text{V}^{(1)}$	H11A617A	40		80	%
			H11A617B	63		125	%
			H11A617C	100		200	%
			H11A617D	160		320	%
		$(I_F = 5mA, V_{CE} = 5V^{(1)}$	H11A817	50		600	%
			H11A817A	80		160	%
			H11A817B	130		260	%
			H11A817C	200		400	%
			H11A817D	300		600	%
		$I_F = 1 \text{mA}, V_{CE} = 5 V^{(1)}$	H11A617A	13			%
			H11A617B	22			%
			H11A617C	34			%
			H11A617D	56			%
V _{CE (SAT)}	Collector-Emitter	$I_{\rm C} = 1$ mA, $I_{\rm F} = \pm 20$ mA	814 series			0.2	V
	Saturation Voltage	$I_{C} = 2.5 \text{mA}, I_{F} = 10 \text{mA}$ $I_{C} = 1 \text{mA}, I_{F} = 20 \text{mA}$	617 series			0.4	1
		$I_{C} = I M A, I_{F} = 20 M A$	817 series			0.2	1
AC CHAF	ACTERISTIC						
t _r	Rise Time	$I_{C} = 2mA, V_{CE} = 2 V, R_{L} = 100\Omega^{(2)}$	ALL		4	18	μs
t _f	Fall Time	$I_{\rm C} = 2$ mA, $V_{\rm CE} = 2$ V, $R_{\rm L} = 100 \Omega^{(2)}$	ALL		3	18	μs

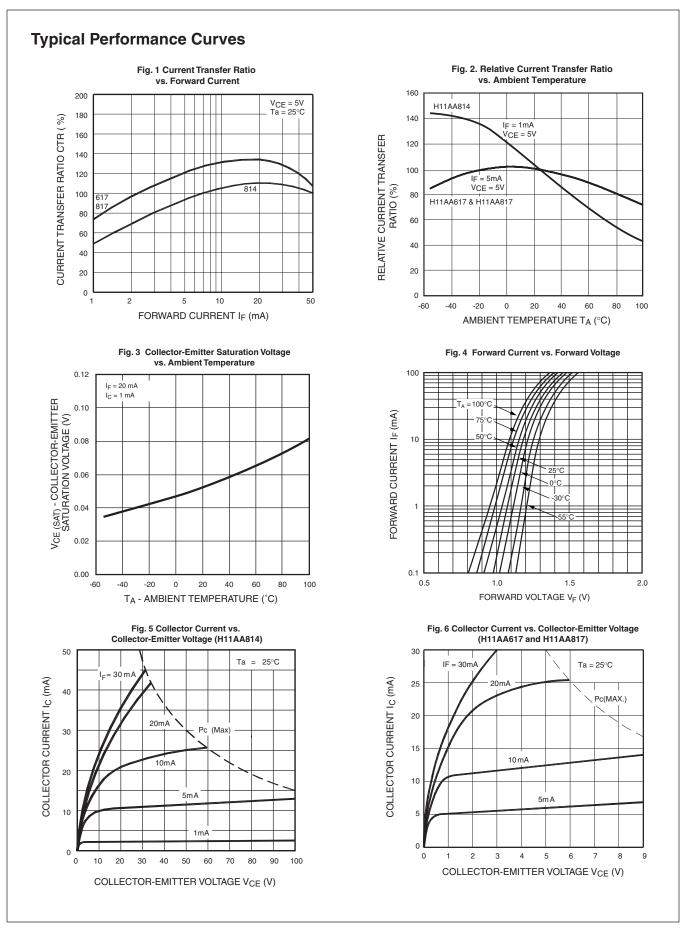
Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage (note 3)	$\begin{array}{l} (f=60Hz,t=1min)\\ (I_{I\text{-}O}\leq 2\mu\text{A}) \end{array}$	5000			Vac(rms)
R _{ISO}	Isolation Resistance	(V _{I-O} = 500 VDC)	5x10 ¹⁰	10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	(V _{I-O} = 0, f = 1 MHz)		0.6	1.0	pf

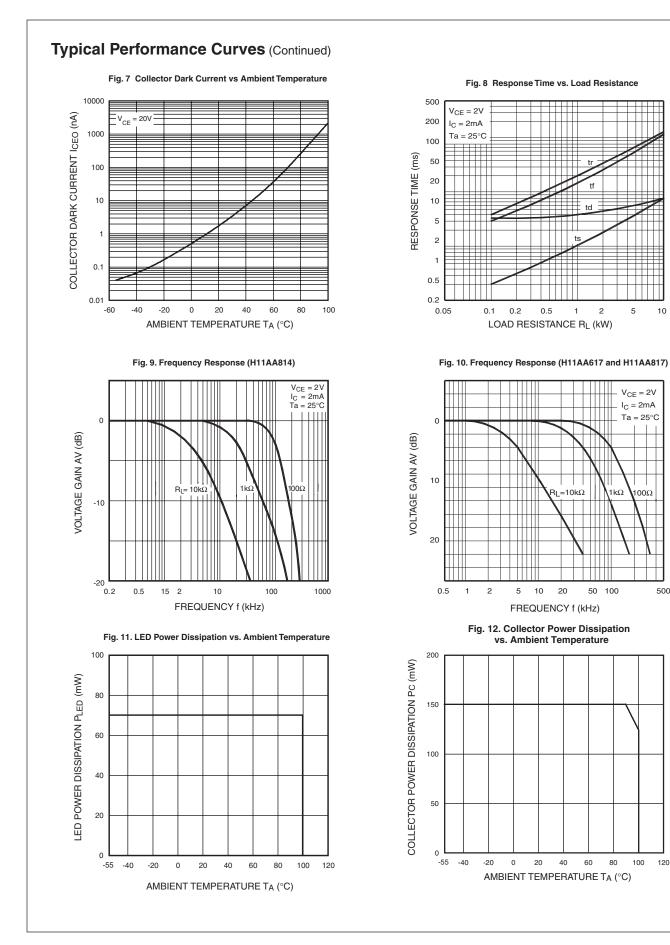
*Typical values at $T_A = 25^{\circ}C$.

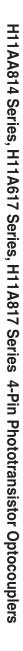
Notes:

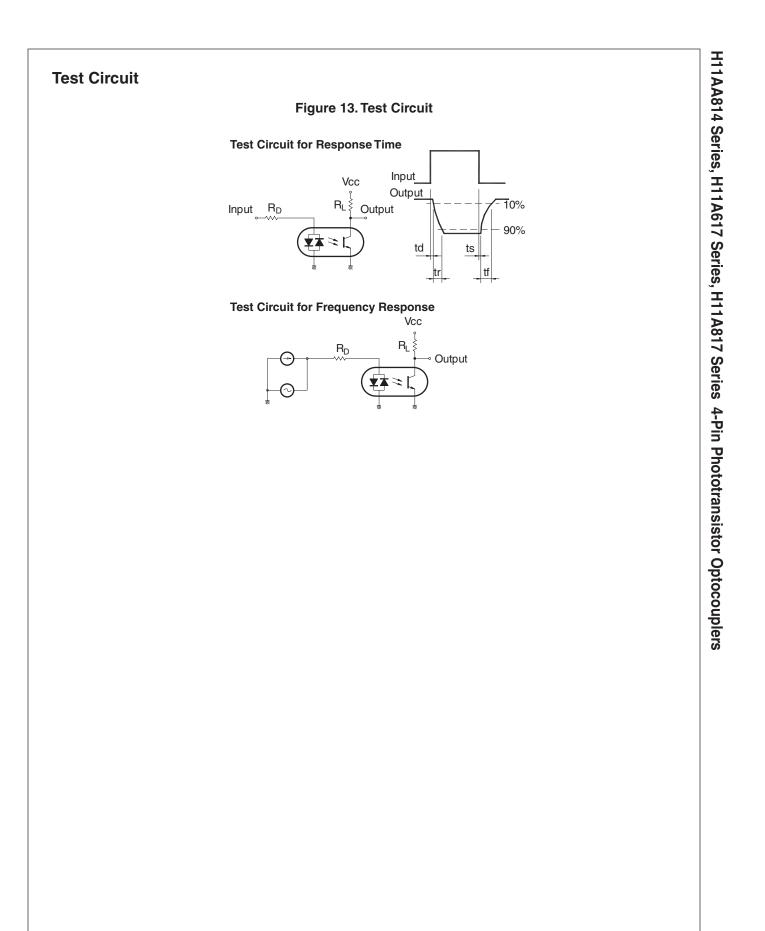
- 1. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 2. For test circuit setup and waveforms, refer to Figure 13.
- 3. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.



4



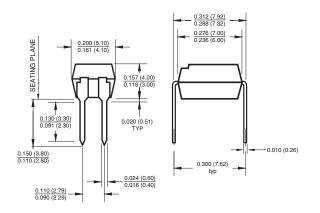




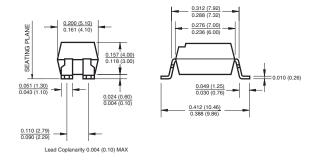
Package Dimensions

H11AA814 Series, H11A617 Series, H11A817 Series 4-Pin Phototransistor Optocouplers

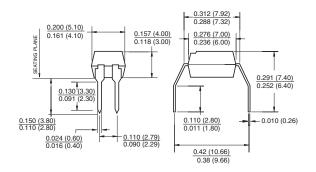
Through Hole



Surface Mount



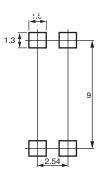
0.4" Lead Spacing



Note:

All dimensions are in inches (millimeters)

Footprint Dimensions (Surface Mount)

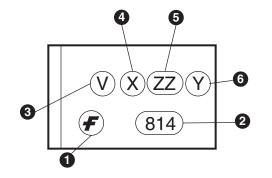


Ordering Information

Part Number Example	Description
H11AA814S	Surface Mount Lead Bend
H11AA814SD	Surface Mount; Tape and reel
H11AA814W	0.4" Lead Spacing
H11AA814300	VDE Approved
H11AA814300W	VDE Approved, 0.4" Lead Spacing
H11AA8143S	VDE Approved, Surface Mount
H11AA8143SD	VDE Approved, Surface Mount, Tape & Reel

*To specify the new construction version which needs 260°C max reflow peak temperature rating: add "NF098" to the end of the part number. The non-NF098 version is rated for 260°C peak reflow temperature only for parts marked with date code 0550 and later.

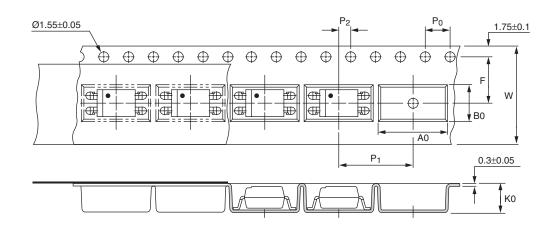
Marking Information



Definiti	ons
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

H11AA814 Series, H11A617 Series, H11A817 Series 4-Pin Phototransistor Optocouplers

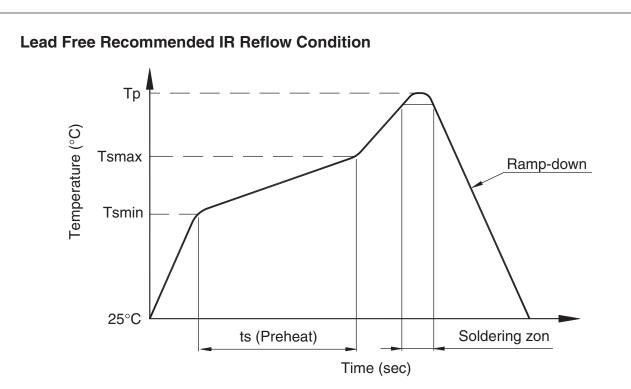
Carrier Tape Specifications



Note:

All dimensions are in millimeters

Description	Symbol	Dimensions in mm (inches)
Tape wide	W	16 ± 0.3 (.63)
Pitch of sprocket holes	P ₀	4 ± 0.1 (.15)
Distance of compartment	F P ₂	7.5 ± 0.1 (.295) 2 ± 0.1 (.079)
Distance of compartment to compartment	P ₁	12 ± 0.1 (.472)
Compartment	A0	10.45 ± 0.1 (.411)
	B0	5.30 ± 0.1 (.209)
	К0	4.25 ± 0.1 (.167)



Profile Feature	Pb-Sn solder assembly	Lead Free assembly
Preheat condition (Tsmin-Tsmax / ts)	100°C ~ 150°C 60 ~ 120 sec	150°C ~ 200°C 60 ~120 sec
Melt soldering zone	183°C 60 ~ 120 sec	217°C 30 ~ 90 sec
Peak temperature (Tp)	240 +0/-5°C	260 +0/-5°C
Ramp-down rate	6°C/sec max.	6°C/sec max.

Recommended Wave Soldering condition

Profile Feature	For all solder assembly
Peak temperature (Tp)	Max 260°C for 10 sec

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

OCX™

POP™

QFET[®]

QS™

OCXPro™

PACMAN™

Power247™

PowerEdge™

PowerSaver™

PowerTrench®

Quiet Series[™]

RapidConfigure™

RapidConnect™

ScalarPump™

µSerDes™

QT Optoelectronics[™]

OPTOLOGIC[®]

OPTOPLANAR™

SILENT SWITCHER®

SMART START™

SPM™

Stealth™

SuperFET™

SuperSOT™-3

SuperSOT™-6

SuperSOT™-8

SvncFET™

TinyBoost™

TinyBuck™

TinyPWM™

TinyLogic®

UHC™

TinyPower™

TINYOPTO™

TruTranslation™

ТСМ™

UniFET™

UltraFET[®]

VCX™

Wire™

ACEx [™] ActiveArray [™] Bottomless [™] Build it Now [™] CoolFET [™]	FACT Quiet Series [™] GlobalOptoisolator [™] GTO [™] HiSeC [™] I ² C [™]
CROSSVOLT™	i-Lo™
DOME™	ImpliedDisconnect [™]
EcoSPARK™	IntelliMAX™
E ² CMOS™	ISOPLANAR™
EnSigna™	LittleFET™
FACT™	MICROCOUPLER™
FAST [®]	MicroFET™
FASTr™	MicroPak™
FPS™	MICROWIRE™
FRFET™	MSX™
	MSXPro™
Across the board. A	round the world.™
The Power Franchis	se [®]

Programmable Active Droop[™]

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification	Product Status	Definition	
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.	
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.	
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.	
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.	
		R	Rev.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor:

 H11A817B300
 H11A817B3S
 H11A817BSD
 H11A817B
 H11A817B300W
 H11A817B3SD
 H11A817BSD

 H11A817BS
 H11A817SD
 H11A817SD
 H11A617B3S
 H11A8173SD
 H11A817A3SD
 H11A817CW
 H11A817A3SD
 H11A817CW
 H11A817ASD
 H11A817CW
 H11A817CW
 H11A817CW
 H11A817CW
 H11A817CW
 H11A817ASD
 H11A817CW
 H11A817CW
 H11A817A3SD
 H11A817CW
 H11A817CW
 H11A817CW
 H11A817CSD
 H11A817CSD